IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

icant : Ohnuma, et al.

Art Unit: 1765

Serial No.: 09/050,182

Examiner: R. Kunemund

: March 26, 1998

Title

: METHOD OF MANUFACTURING A SEMICONDUCTOR DEVICE

## BOX AF

Commissioner for Patents Washington, D.C. 20231

## AMENDMENT AFTER FINAL OFFICE ACTION

In response to the action mailed March 27, 2000, please amend the application as follows:

In the Claims:

Please amend claims 1-3, 5, 9-11, 13, 17-19, 21, 45-46, and 52-53.

(Amended) A method of manufacturing a semiconductor

device, said method comprising the steps of:

forming an amorphous semiconductor film comprising silicon

over a substrate having an insulating surface;

CERTIFICATE OF MAILING BY FIRST CLASS MAIL

I hereby certify under 37 CFR §1.8(a) that this correspondence is being deposited with the United States Postal Service as first class mail with sufficient postage on the date indicated below and is addressed to the Commissioner for Patents, Washington, D.C. 20231.

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